AVD090F

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD090F** is Designed for

FEATURES:

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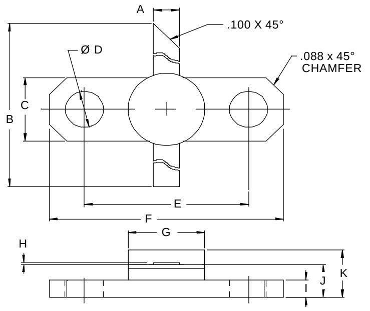
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	6.5 A PEAK
V_{CB}	55 V
P_{DISS}	250 W PEAK
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	0.6 ^{O}C/W

PACKAGE STYLE .250 2L FLG (B)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

ORDER CODE: ASI10562

CHARACTERISTICS $T_C = 25\ ^OC$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 mA	65			**V**
BV_{CER}	I_C = 10 mA R_{BE} = 10 Ω	65			**V**
BV_{EBO}	I_E = 1 mA	3.5			**V**
I_{CES}	V_{CB} = 50 V			6.25	**mA**
h_{FE}	V_{CE} = 5.0 V I_C = 500 mA	15		120	**---**
P_G	V_{CC} = 50 V P_{OUT} = 90 W f = 1025 - 1150 MHz	8.5			**dB**
η_C		35			**%**